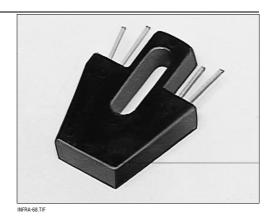
Reflective Sensor

FEATURES

- · Phototransistor output
- Focused for maximum response
- · Ambient light and dust protective filter



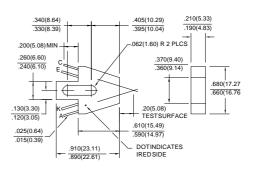
DESCRIPTION

The HOA1405 series consists of an infrared emitting diode and an NPN silicon phototransistor encased side-by-side on converging optical axes in a black thermoplastic housing. The phototransistor responds to radiation from the IRED only when a reflective object passes within its field of view. The HOA1405 series employs an IR transmissive filter to minimize the effects of visible ambient light and to provide a smooth optical face which prevents the accumulation of airborne contaminants in the optical path. The HOA1405 series contains plastic molded components. For additional component information see SEP8505 and SDP8405.

Housing material is polyester. Housings are soluble in chlorinated hydrocarbons and ketones. Recommended cleaning agents are methanol and isopropanol.

OUTLINE DIMENSIONS in inches (mm)

Tolerance 3 plc decimals $\pm 0.010(0.25)$ 2 plc decimals $\pm 0.020(0.51)$



DIM_032.ds4



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Reflective Sensor

ELECTRICAL CHARACTERISTICS (25°C unless otherwise noted)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITIONS
IR EMITTER						
Forward Voltage	VF			1.6	V	I _F =20 mA
Reverse Leakage Current	IR			10	μΑ	V _R =3 V
DETECTOR						
Collector-Emitter Breakdown Voltage	V _(BR) ceo	30			V	Ic=100 μA
Emitter-Collector Breakdown Voltage	V _{(BR)ECO}	5.0			V	I _E =100 μA
Collector Dark Current	ICEO			100	nA	V _{CE} =10 V, I _F =0
COUPLED CHARACTERISTICS On-State Collector Current HOA1405-001 HOA1405-002	Ic(on)	0.2 0.8			mA	VcE=5 V I _F =30 mA
Collector-Emitter Saturation Voltage	VCE(SAT)				V	I _F =30 mA ⁽¹⁾
HOA1405-001	V _(BR) CEO			0.4		Ic=30 μA
HOA1405-002				0.4		Ic=100 μA
Rise And Fall Time	t _r , t _f		15		μs	V _{CC} =5 V, I _C =1 mA R_L =1000 Ω

Notes
1. Test surface is a Eastman Kodak neutral white card with 90% diffuse reflectance located 0.20 in. (5.0 mm) from the front surface of the device.

ABSOLUTE MAXIMUM RATINGS

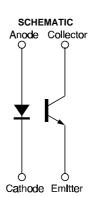
(25°C Free-Air Temperature unless otherwise noted)

Operating Temperature Range -40°C to 85°C -40°C to 85°C Storage Temperature Range Soldering Temperature (5 sec) 240°C

IR EMITTER

Power Dissipation 70 mW (1) Reverse Voltage 3 V Continuous Forward Current 50 mA DETECTOR 30 V Collector-Emitter Voltage **Emitter-Collector Voltage** 70 mW (1) Power Dissipation

1. Derate linearly at 0.18 mW/°C above 25°C.



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Reflective Sensor

Fig. 1 IRED Forward Bias Characteristics

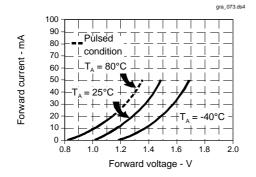


Fig. 2 Non-Saturated Switching Time vs Load Resistance gra_074.ds4

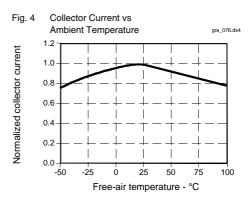
Fig. 3 Dark Current vs
Temperature

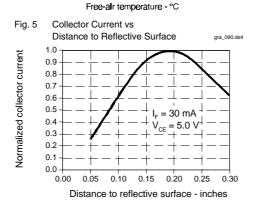
1000
VCE = 15 V
H = 0

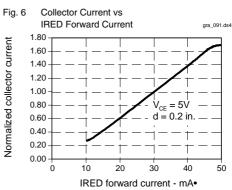
0.1

0.01

-40 -20 0 20 40 60 80 100







All Performance Curves Show Typical Values

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